

PNP 5 GHz wideband transistor

BFQ149

DESCRIPTION

PNP transistor in a SOT89 envelope. It is intended for use in UHF applications such as broadband aerial amplifiers (30 to 860 MHz) and in microwave amplifiers such as radar systems, spectrum analysers, etc., using SMD technology.

PINNING

PIN	DESCRIPTION
Code: FG	
1	emitter
2	collector
3	base

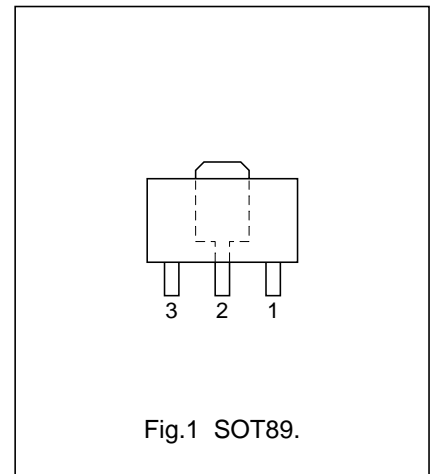


Fig.1 SOT89.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CE0}	collector-emitter voltage	open base	–	–	–15	V
I_C	DC collector current		–	–	–100	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$ (note 1)	–	–	1	W
h_{FE}	DC current gain	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $T_j = 25\text{ °C}$	20	50	–	
f_T	transition frequency	$I_C = -75\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_j = 25\text{ °C}$	4	5	–	GHz
G_{UM}	maximum unilateral power gain	$I_C = -50\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	12	–	dB
F	noise figure	$I_C = -50\text{ mA}$; $V_{CE} = -10\text{ V}$; $R_s = 60\text{ }\Omega$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	3.75	–	dB

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–20	V
V_{CE0}	collector-emitter voltage	open base	–	–15	V
V_{EBO}	emitter-base voltage	open collector	–	–3	V
I_C	DC collector current		–	–100	mA
I_{CM}	peak collector current	$f > 1\text{ MHz}$	–	–150	mA
P_{tot}	total power dissipation	up to $T_s = 135\text{ °C}$ (note 1)	–	1	W
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	150	°C

Note

- T_s is the temperature at the soldering point of the collector tab.

PNP 5 GHz wideband transistor

BFQ149

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j-s}$	thermal resistance from junction to soldering point	up to $T_s = 135\text{ °C}$ (note 1)	40 K/W

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = -10\text{ V}$;	–	–	100	nA
h_{FE}	DC current gain	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$	20	50	–	
f_T	transition frequency	$I_C = -70\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	4	5	–	GHz
C_c	collector capacitance	$I_E = 0$; $V_{CB} = -10\text{ V}$; $f = 1\text{ MHz}$	–	2	–	pF
C_e	emitter capacitance	$I_C = 0$; $V_{EB} = -0.5\text{ V}$; $f = 1\text{ MHz}$	–	4	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = -10\text{ V}$; $f = 1\text{ MHz}$	–	1.7	–	pF
G_{UM}	maximum unilateral power gain (note 1)	$I_C = -50\text{ mA}$; $V_{CE} = -10\text{ V}$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	12	–	dB
F	noise figure	$I_C = -50\text{ mA}$; $V_{CE} = -10\text{ V}$; $R_s = 60\text{ }\Omega$; $f = 500\text{ MHz}$; $T_{amb} = 25\text{ °C}$	–	3.75	–	dB

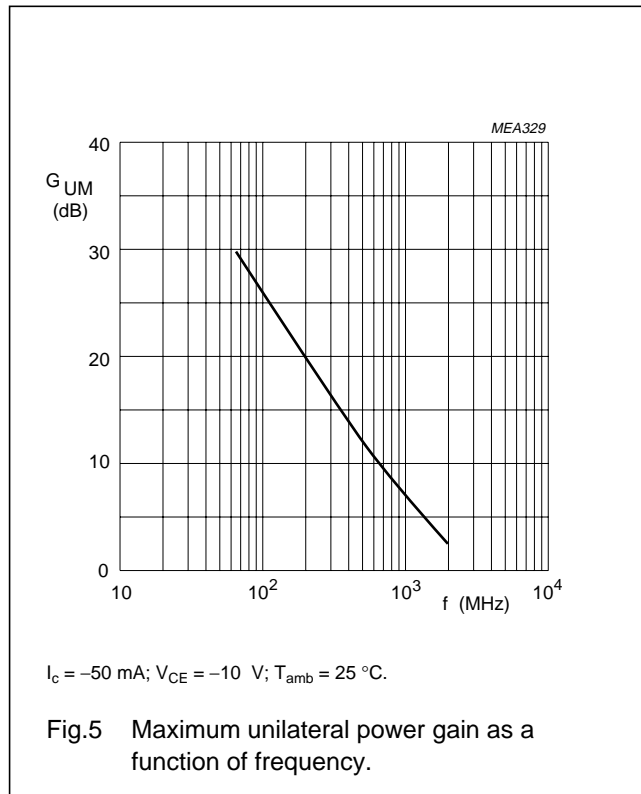
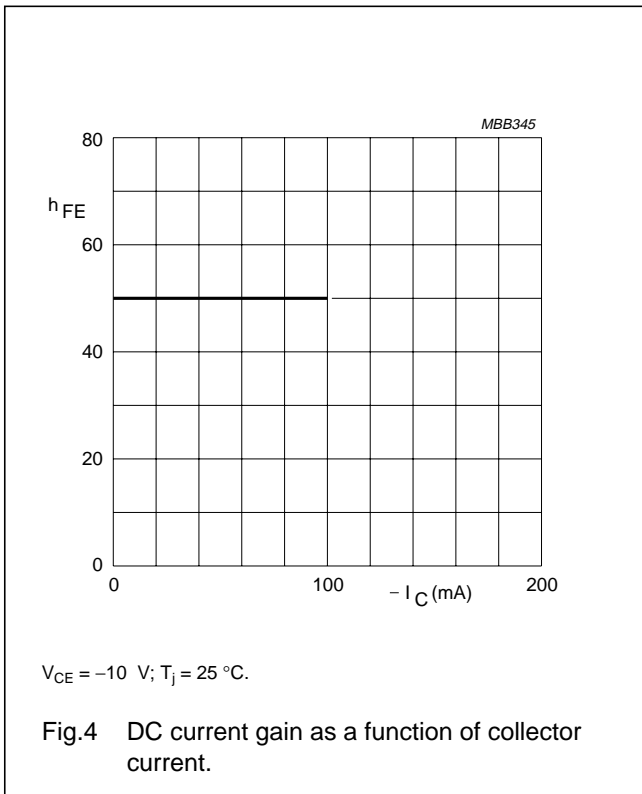
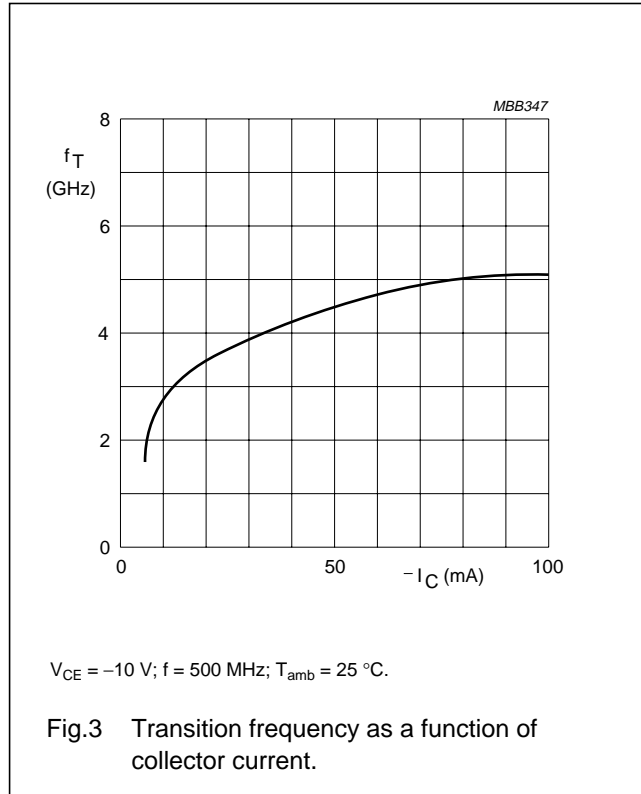
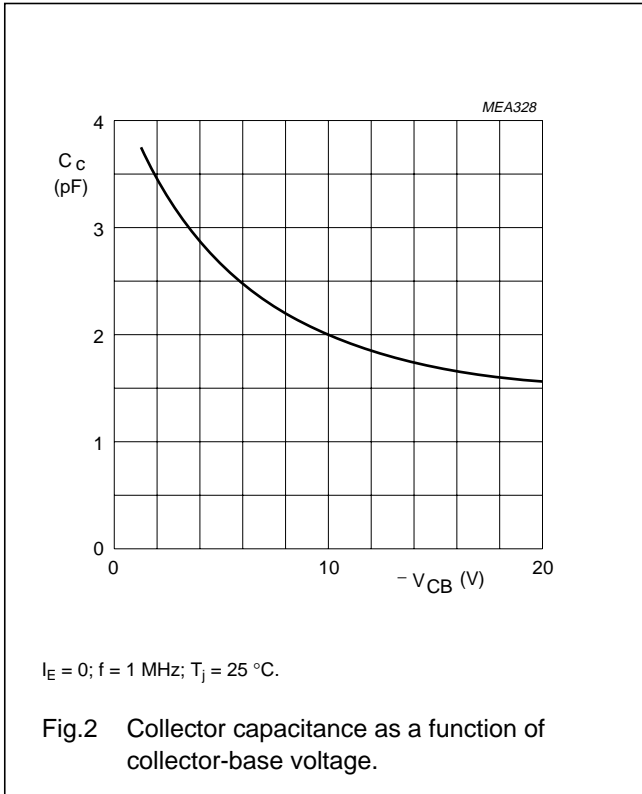
Note

- G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \left(\frac{|S_{21}|^2}{(1 - |S_{11}|^2)(1 - |S_{22}|^2)} \right) \text{ dB.}$$

PNP 5 GHz wideband transistor

BFQ149



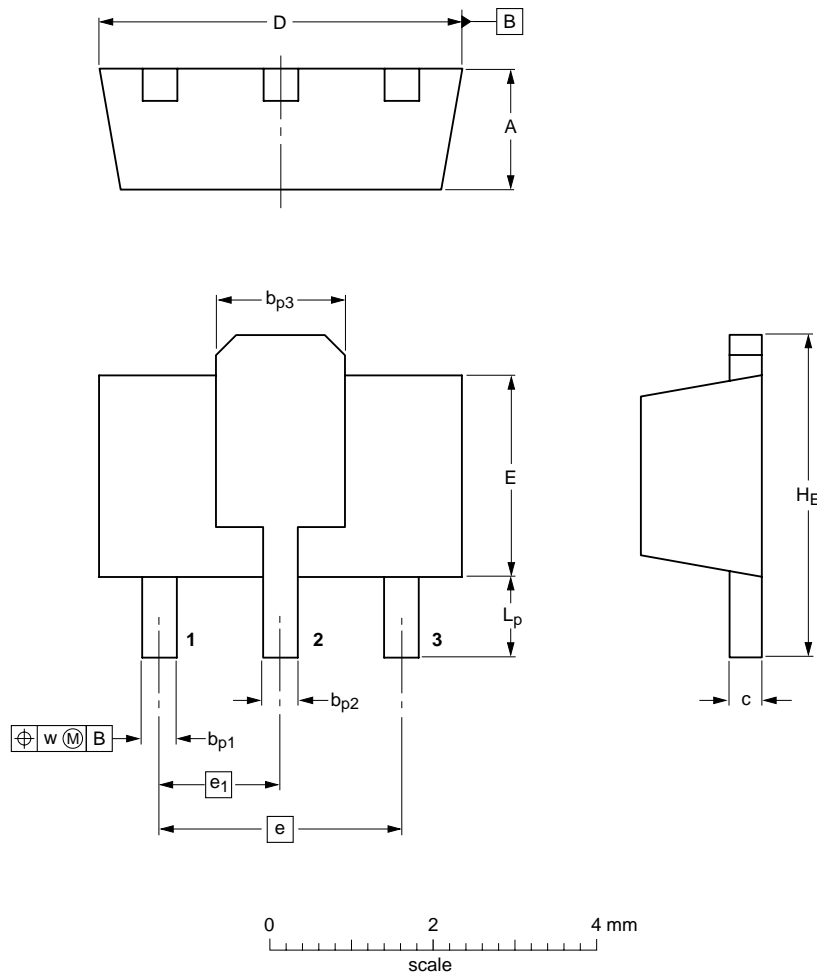
PNP 5 GHz wideband transistor

BFQ149

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		06-03-16 06-08-29

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or

malfunction of a NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at <http://www.nxp.com/profile/terms>, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

Contact information

For additional information, please visit: <http://www.nxp.com>

For sales office addresses, send an email to: salesaddresses@nxp.com

Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFQ149_N_3	20070928	Product data sheet	-	BFQ149_CNV_2
Modifications:	• Fig. 1 and package outline updated			
BFQ149_CNV_2	19950901	Product specification	-	-

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

founded by

PHILIPS

© NXP B.V. 2007.

All rights reserved.

For more information, please visit: <http://www.nxp.com>

For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 28 September 2007

Document identifier: BFQ149_N_3